

7.10-7.90GHz 5-Watt Internally-Matched Power FET

FEATURES

- 7.10-7.90GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +37.5 dBm Output Power at 1dB Compression
- 8.5 dB Power Gain at 1dB Compression
- 35% Power Added Efficiency
- -46 dBc IM3 at PO = 25.5 dBm SCL
- 100% Tested for DC, RF, and R_{TH}





Caution! ESD sensitive device.

ELECTRICAL CHARACTERISTICS (T_a = 25°C)

SYMBOL	PARAMETERS/TEST CONDITIONS ¹	MIN	TYP	MAX	UNITS
P _{1dB}	Output Power at 1dB Compression $f = 7.10-7.90GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 1600\text{mA}$	36.5	37.5		dBm
G _{1dB}	Gain at 1dB Compression $f = 7.10-7.90GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 1600\text{mA}$	7.5	8.5		dB
ΔG	Gain Flatness $f = 7.10-7.90GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 1600\text{mA}$			±0.6	dB
PAE	Power Added Efficiency at 1dB Compression $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 1600 \text{mA}$ f = 7.10-7.90GHz		35		%
Id_{1dB}	Drain Current at 1dB Compression f = 7.10-7.90GHz		1600	2000	mA
IM3	Output 3rd Order Intermodulation Distortion $\Delta f = 10$ MHz 2-Tone Test; Pout = 25.5 dBm S.C.L ² $V_{DS} = 10$ V, $I_{DSQ} \approx 65\%$ IDSS $f = 7.90$ GHz	-43	-46		dBc
I _{DSS}	Saturated Drain Current $V_{DS} = 3 \text{ V}, V_{GS} = 0 \text{ V}$		2900	3500	mA
V_P	Pinch-off Voltage $V_{DS} = 3 \text{ V}, I_{DS} = 30 \text{ mA}$		-2.5	-4.0	V
R _{TH}	Thermal Resistance ³		5.0	5.5	°C/W

Note: 1. Tested with 100 Ohm gate resistor.

2. S.C.L. = Single Carrier Level.

3. Overall Rth depends on case mounting.

ABSOLUTE MAXIMUM RATING FOR EFE

SYMBOLS	PARAMETERS	ABSOLUTE ¹	CONTINUOUS ²	
Vds	Drain-Source Voltage	15V	10V	
Vgs	Gate-Source Voltage	-5V	-4V	
lgf	Forward Gate Current	68mA	20.4mA	
lgr	Reverse Gate Current	-13.6mA	-3.4mA	
Pin	Input Power	37dBm	@ 3dB Compression	
Tch	Channel Temperature	175C	175C	
Tstg	Storage Temperature	-65C to +175C	-65C to +175C	
Pt	Total Power Dissipation	27W	27W	

Note: 1. Exceeding any of the above ratings may result in permanent damage.

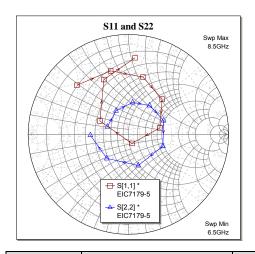
^{2.} Exceeding any of the above ratings may reduce MTTF below design goals.

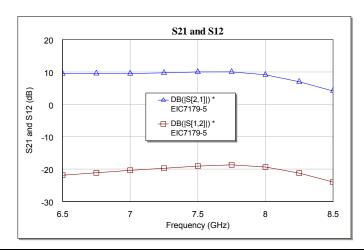


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PERFORMANCE DATA

Typical S-Parameters (T= 25°C, 50 Ω system, de-embedded to edge of package) V_{DS} = 10 V, I_{DSQ} \approx 1600mA



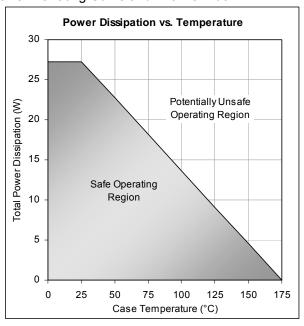


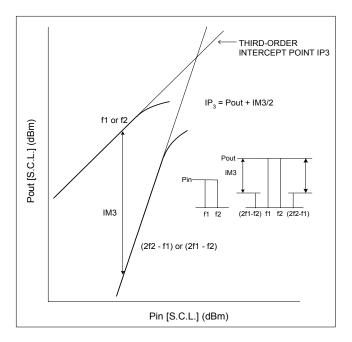
FREQ	S	S11 S21 S12		12	S22			
(GHz)	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
6.25	0.752	168.140	2.901	-7.820	0.073	-64.840	0.232	-147.530
6.50	0.711	136.260	2.974	-39.130	0.081	-97.090	0.224	159.760
6.75	0.659	105.510	3.004	-70.350	0.088	-127.140	0.267	117.460
7.00	0.591	75.820	2.986	-100.630	0.096	-156.850	0.322	82.450
7.25	0.487	46.300	3.063	-131.620	0.103	172.760	0.358	53.770
7.50	0.320	11.650	3.161	-165.600	0.111	140.350	0.377	21.450
7.75	0.097	-69.360	3.168	156.190	0.116	103.520	0.364	-18.780
8.00	0.315	154.860	2.860	113.990	0.108	62.710	0.326	-72.420
8.25	0.600	114.000	2.233	73.400	0.087	23.160	0.323	-131.860
8.50	0.769	85.120	1.607	38.360	0.063	-9.110	0.379	-178.690
8.75	0.843	64.260	1.123	9.490	0.046	-36.130	0.455	151.440



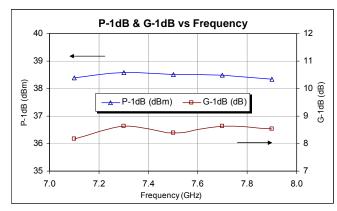
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Power De-rating Curve and IM3 Definition

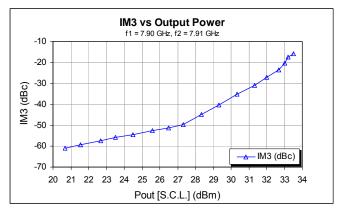




Typical Power Data (V_{DS} = 10 V, I_{DSQ} = 1600 mA)



Typical IM3 Data (V_{DS} = 10 V, I_{DSQ} ≈ 65% IDSS)



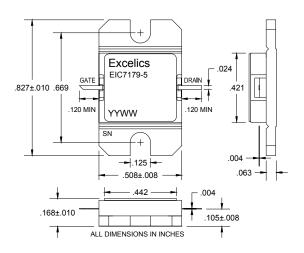


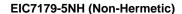
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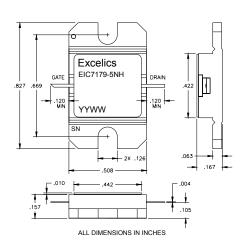
PACKAGES OUTLINE

Dimensions in inches, Tolerance + .005 unless otherwise specified

EIC7179-5 (Hermetic)









Caution! ESD sensitive device.



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ORDERING INFORMATION

Part Number	Packages	Grade ¹	f _{Test} (GHz)	P _{1dB} (min)	IM ₃ (min) ²
EIC7179-5	Hermetic	Industrial	7.10-7.90GHz	36.5	-43
EIC7179-5NH	Non-Hermetic	Industrial	7.10-7.90GHz	36.5	-43

Notes:

- 1. Contact factory for military and hi-rel grades.
- 2. Exact test conditions are specified in "Electrical Characteristics" table.

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